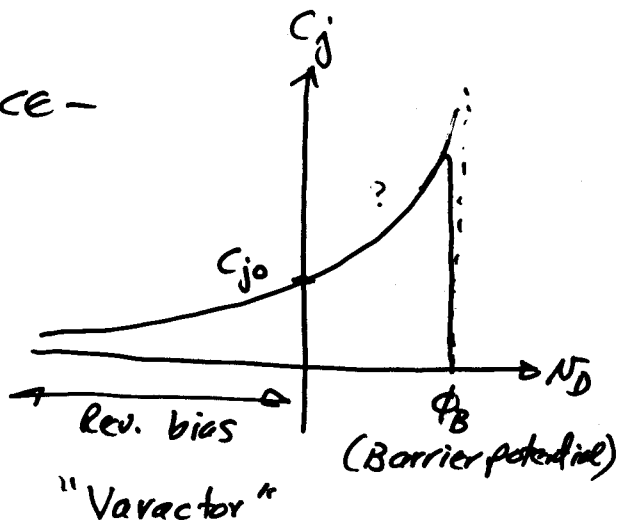
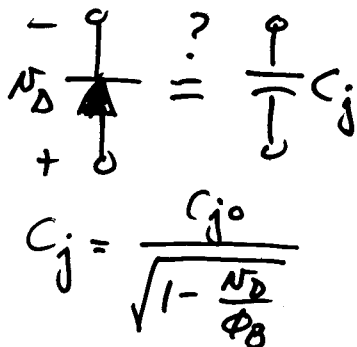


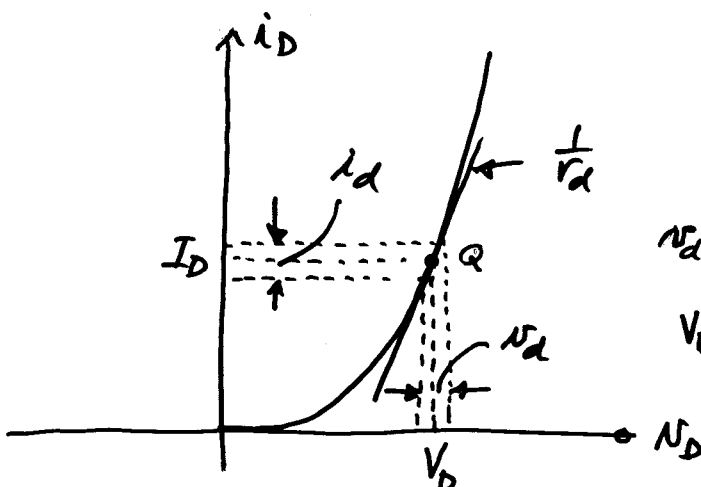
Diodes - Cont'd

Depletion Capacitance -
Reverse biased

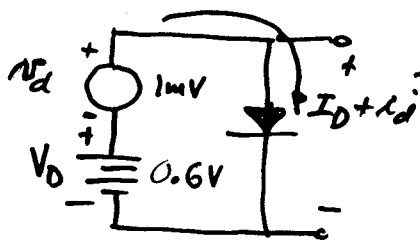


Large & Small Signal Models

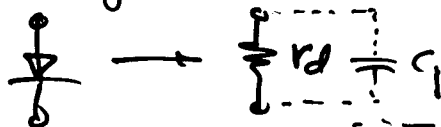
Consider the I-V Diode Plot



$$i_D = I_S \left[\exp\left(\frac{v_D}{V_T}\right) - 1 \right]$$



Small signal model of a diode

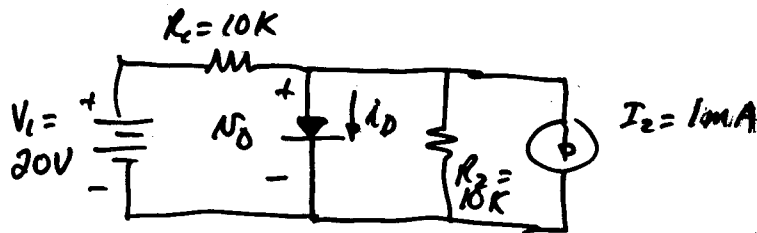


$$\frac{1}{r_d} = g_d = \left. \frac{\partial i_D}{\partial v_D} \right|_Q \approx \left(\frac{I_S}{V_T} \exp\left(\frac{v_D}{V_T}\right) \right) = \frac{I_D}{V_T}$$

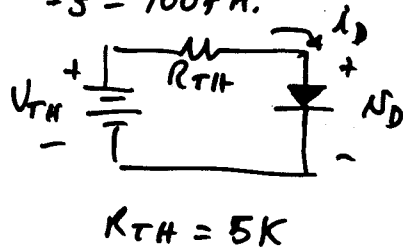
Assumed fwd bias

$$V_T = \frac{kT}{q} \approx 25mV$$

Diode Example



a.) Find the dc operating point if $V_T = 25mV$, $n = 1$ and $I_S = 100fA$.



$$V_{TH} = 20V \frac{R_1}{R_1 + R_2} - (10K // 10K) 1mA$$

$$V_{TH} = 10V - 5V = 5V$$

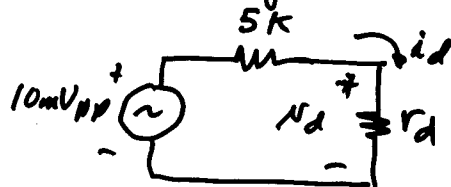
$$R_{TH} = 5K$$

Solution -

Guess at v_D	$i_D = \frac{5V - v_D}{5K}$	$i_D = I_S \exp\left(\frac{v_D}{V_T}\right)$
0.6	0.88mA	2.331mA
0.57	0.886mA	0.798mA
\vdots	\vdots	\vdots
<u>0.5726</u>	<u>0.88545mA</u>	0.88528mA

b.) If the 20V voltage source has a peak-to-peak sinusoidal signal of 10mV_{pp} placed in series with it, find the p-p value of v_D and i_D of the diode

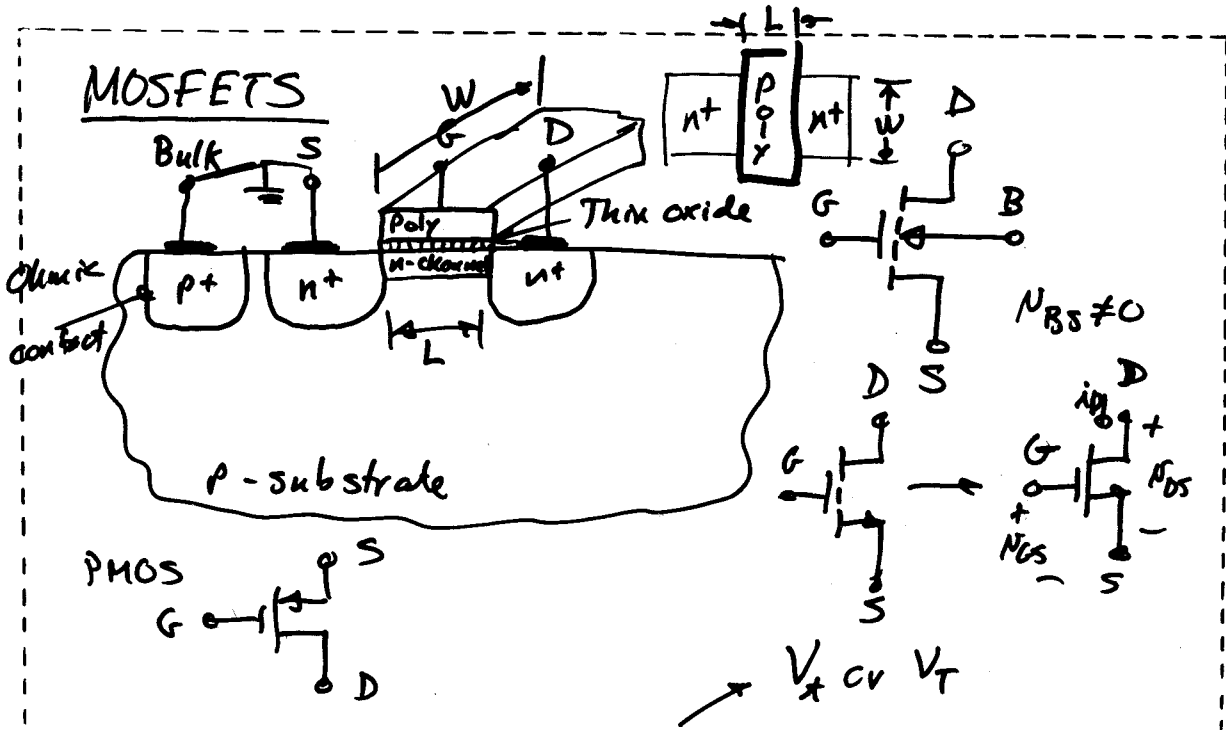
Small signal model:



$$r_d = \frac{V_T}{I_D} = \frac{25mV}{0.885mA} \approx 28.5\Omega$$

$$i_d = \frac{10mV}{5028.5\Omega} \approx \underline{\underline{2\mu A_{pp}}}$$

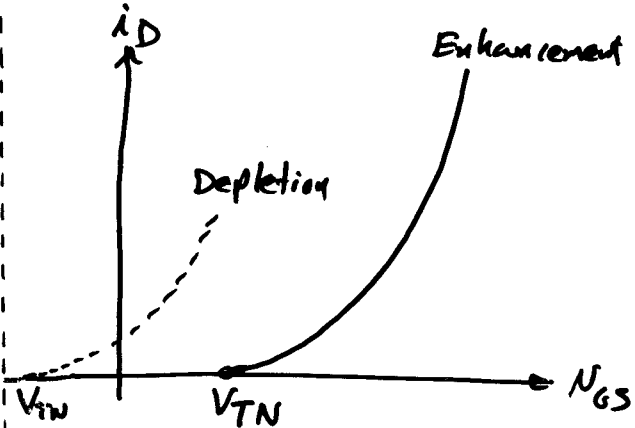
$$v_d = i_d r_d \approx \underline{\underline{57\mu V_{pp}}}$$



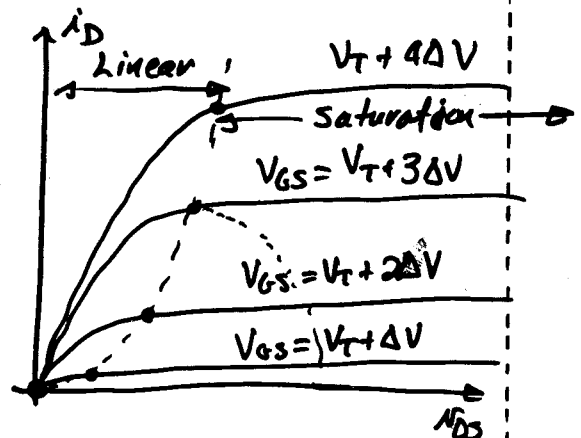
Enhancement - Threshold > 0 for NMOS
 Depletion - Threshold for NMOS < 0

Graphical Model for NMOS

Transconductance Char.:



Output Characteristic:



Math Model

- 1.) Linear region - $i_D = K_n' \frac{W}{L} (V_{GS} - V_{TN} - \frac{V_{DS}}{2}) V_{DS} (1 + \lambda V_{DS})$
 where $V_{GS} - V_{TN} < V_{DS}$
- 2.) Saturation region - $i_D = \frac{K_n'}{2} \frac{W}{L} (V_{GS} - V_{TN})^2 (1 + \lambda V_{DS})$